

描述 / Descriptions

SOT-23 塑封封装 硅 PNP 数字三极管。Silicon PNP Digital transistor in a SOT-23 Plastic Package.

特征 / Features

内装偏置电阻，简化线路设计，减少元件和制造流程。

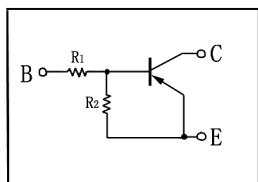
With built-in bias resistors, simplify circuit design, reduce a quantity of parts and manufacturing process.

用途 / Applications

用于开关、界面电路以及驱动电路中。

Switching applications, interface circuit and driver circuit applications.

内部等效电路 / Equivalent Circuit



引脚排列 / Pinning



PIN 1 : Base

PIN 2 : Emitter

PIN 3 : Collector

放大及印章代码 / h_{FE} Classifications & Marking

Marking	H14
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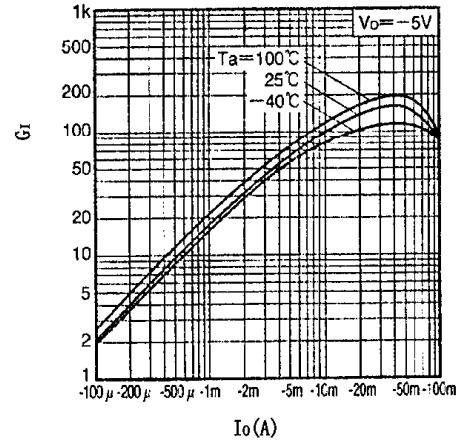
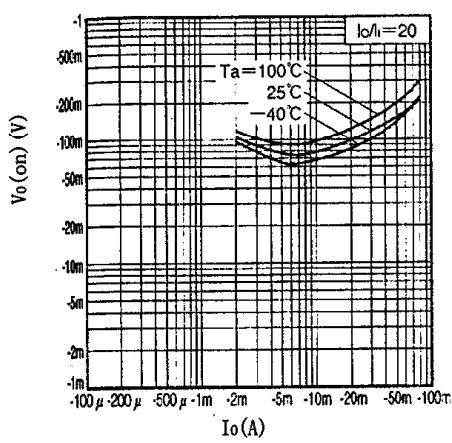
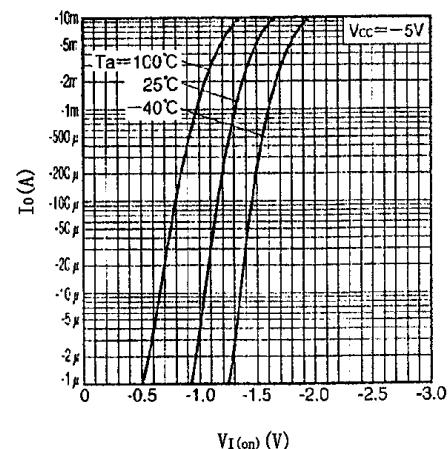
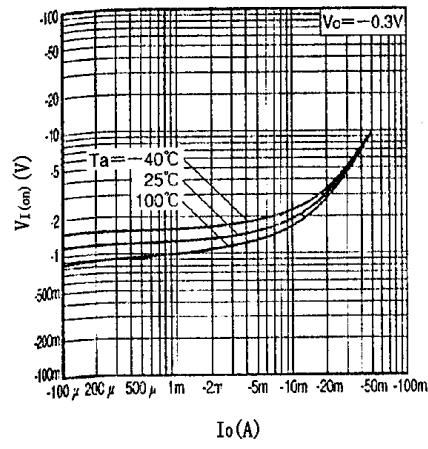
极限参数 / Absolute Maximum Ratings(Ta=25°C)

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Output Voltage	V _{CC}	-50	V
Input Voltage	V _{IN}	-40	V
		10	V
Output Current	I _C	-100	mA
	I _O	-50	mA
Power Dissipation	P _C	200	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-55~150	°C

电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Input Voltage(OFF)	V _{I(off)}	V _{CC} =-5.0V I _O =-100μA			-0.5	V
Input Voltage(ON)	V _{I(on)}	V _O =-0.3V I _O =-10mA	-3			V
Output Voltage	V _{O(on)}	I _O =-10mA I _I =-0.5mA			-0.3	V
Input Voltage	I _I	V _I =-5.0V			-0.88	mA
Output Cut-off Current	I _{O(off)}	V _{CC} =-50V V _I =0V			-0.5	μA
DC Current Gain	G _I	V _O =-5.0V I _O =-5.0mA	30			
Transition Frequency	f _T	V _{CE} =-10V I _C =-5.0 mA f=100MHz		250		MHz
Resistance1	R ₁		7	10	13	KΩ
Resistance Ratio	R _{2/R₁}		0.8	1	1.2	

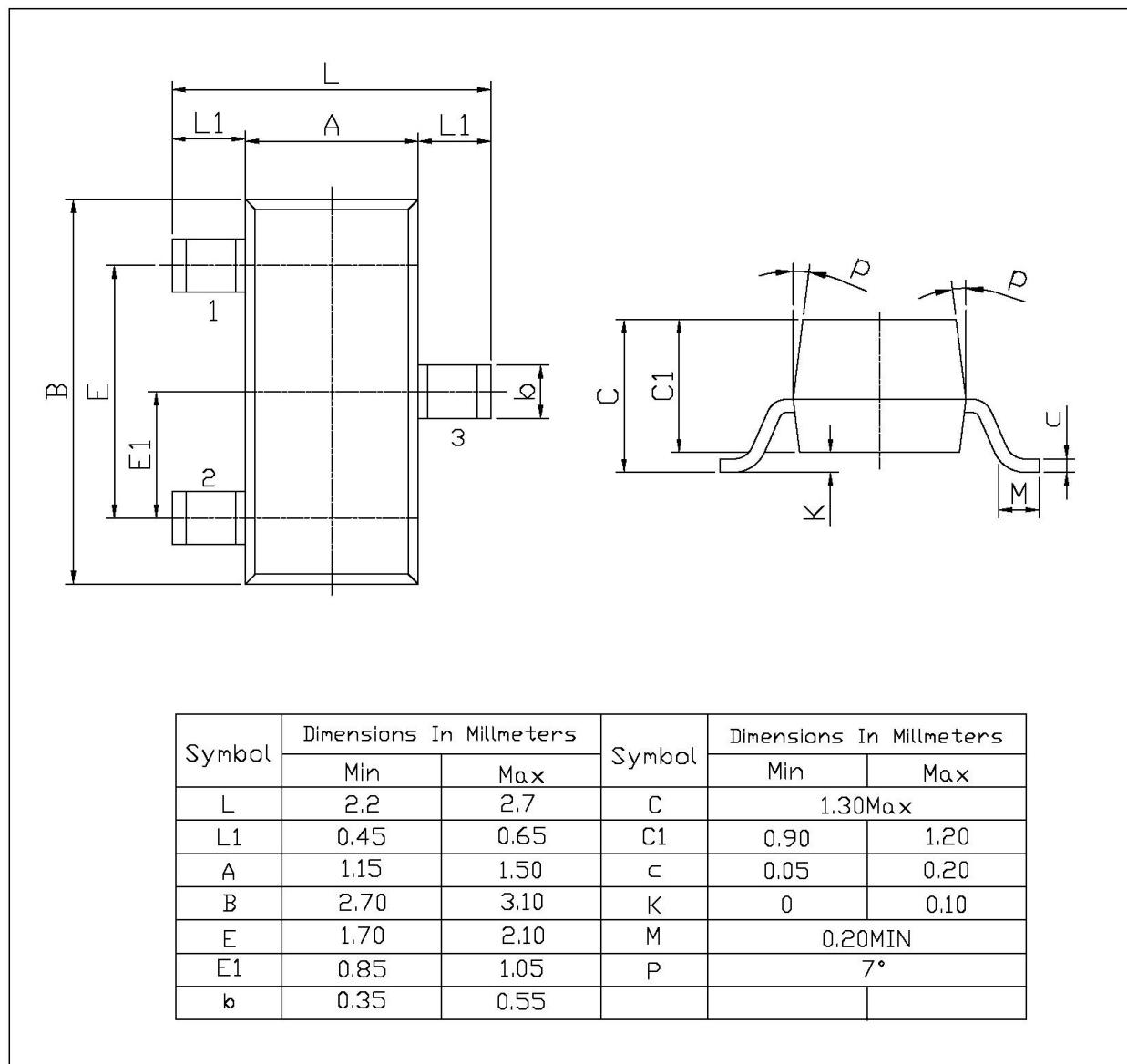
电参数曲线图 / Electrical Characteristic Curve



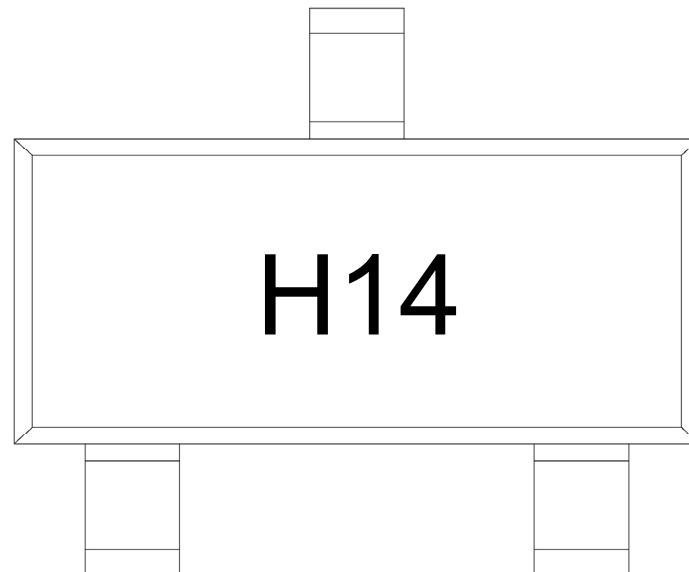
外形尺寸图 / Package Dimensions

SOT-23

单位: mm



印章说明 / Marking Instructions



说明 :

H : 为公司代码

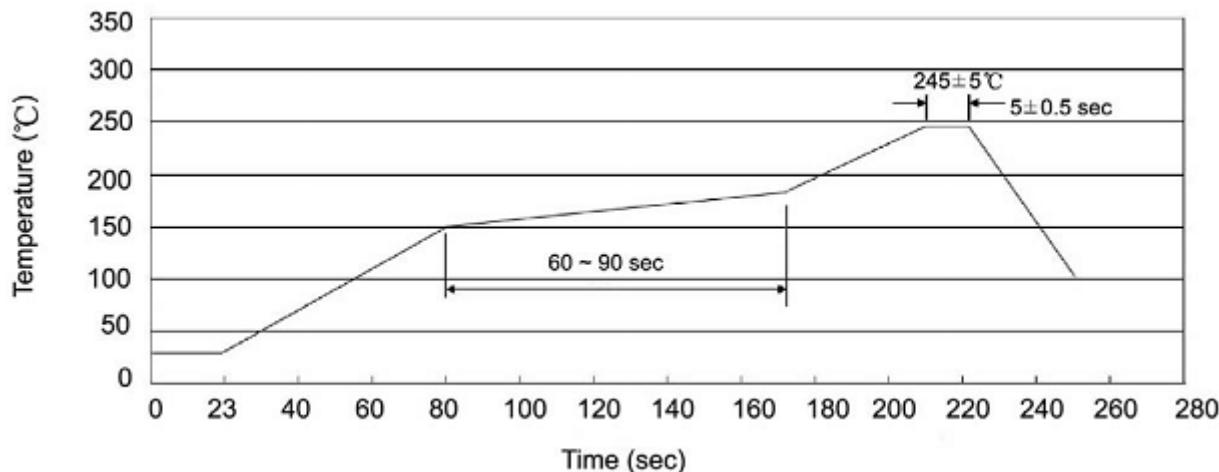
14 : 为型号代码

Note:

H : Company Code

14 : Product Type Code

回流焊温度曲线图(无铅) / Temperature Profile for IR Reflow Soldering(Pb-Free)



说明：

- 1、预热温度 $25 \sim 150^\circ\text{C}$ ，时间 $60 \sim 90\text{sec}$;
- 2、峰值温度 $245 \pm 5^\circ\text{C}$ ，时间持续为 $5 \pm 0.5\text{sec}$;
- 3、焊接制程冷却速度为 $2 \sim 10^\circ\text{C/sec}$.

Note:

- 1.Preheating: $25\sim150^\circ\text{C}$, Time: $60\sim90\text{sec}$.
- 2.Peak Temp.: $245\pm5^\circ\text{C}$, Duration: $5\pm0.5\text{sec}$.
3. Cooling Speed: $2\sim10^\circ\text{C/sec}$.

耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度 : $260 \pm 5^\circ\text{C}$

时间 : $10 \pm 1\text{ sec}$.

Temp.: $260 \pm 5^\circ\text{C}$

Time: $10 \pm 1\text{ sec}$

包装规格 / Packaging SPEC.

卷盘包装 / REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
SOT-23	3,000	10	30,000	6	180,000	7" x8	180x120x180	390x385x205

使用说明 / Notices

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[DTC115TKAT146](#) [DTC124TETL](#) [DTC144VUAT106](#) [MUN5241T1G](#) [BCR158WH6327XTSA1](#) [NSBA114TDP6T5G](#) [NSBA123EF3T5G](#)
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[DTC123TM3T5G](#) [DTA114ECA-TP](#) [DTA113EM3T5G](#) [DTC113EM3T5G](#)